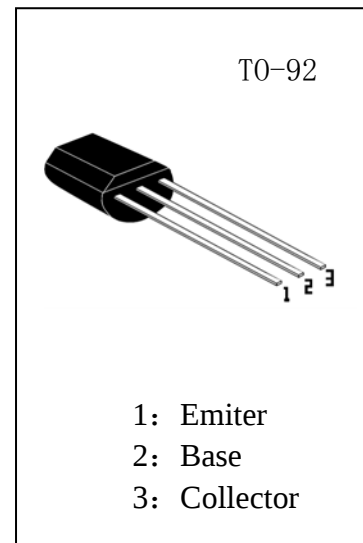


AMPLIFIER TRANSISTOR

- $V_{ce0} = -150V$
- 高耗散功率 $P_c = 625mW$
- 与 2N5551 对管

极限参数(Absolute Maximum Ratings) $T_a = 25^{\circ}C$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	-160	V
Collector-Emitter Voltage	V_{ceo}	-150	V
Emitter-Base Voltage	V_{ebo}	-5	V
Collector Current	I_c	600	mA
Collector Dissipation	P_c	625	m W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55~150	$^{\circ}C$


电性能(Electrical Characteristic) $T_a = 25^{\circ}C$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c = -100\mu A, I_e = 0$	-160			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c = -1mA, I_b = 0$	-150			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e = -10\mu A, I_c = 0$	-5			V
I_{cbo}	Collector Cutoff Current	$V_{cb} = -120V, I_e = 0$			-50	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb} = -3V, I_c = 0$			-50	nA
I_{ceo}	Collector Cutoff Current	$V_{ce} = -150V, I_b = 0$			-1	μA
$V_{ce(sat)1}$	Collector-Emitter Saturation Voltage	$I_c = -10mA, I_b = -1mA$		0.08	-0.2	V
$V_{ce(sat)2}$	Collector-Emitter Saturation Voltage	$I_c = -50mA, I_b = -5mA$		0.12	-0.5	V
$V_{be(sat)1}$	Base-Emitter Saturation Voltage	$I_c = -10mA, I_b = -1mA$		0.76	-0.9	V
$V_{be(sat)2}$	Base-Emitter Saturation Voltage	$I_c = -50mA, I_b = -5mA$		0.86	-1.0	V
H_{fe1}	DC Current Gain	$V_{ce} = -5V, I_c = -1mA$	30			
H_{fe2}	DC Current Gain	$V_{ce} = -5V, I_c = -10mA$	80		300	
H_{fe3}	DC Current Gain	$V_{ce} = -5V, I_c = -50mA$	50			
C_{ob}	Output Capacitance	$V_{cb} = -10V, I_e = 0, f = 1MHz$			6	PF
f_T	Current Gain-Bandwidth product	$V_{ce} = -10V, I_c = -10mA,$	100		400	MHz
NF	Noise Figure	$I_c = -250\mu A, V_{ce} = -5V$ $F = 10Hz \sim 15.7kHz, R_s = 1k\Omega$			9	dB

CLASS	B	C	D	E
Hfe2	80-100	100-150	150-200	200-300